

TrenchMOS™ transistor
Standard level FET

PHT11N06T

GENERAL DESCRIPTION

N-channel enhancement mode logic level field-effect power transistor in a plastic envelope suitable for surface mounting. Using 'trench' technology the device features very low on-state resistance and has integral zener diodes giving ESD protection. It is intended for use in DC-DC converters and general purpose switching applications.

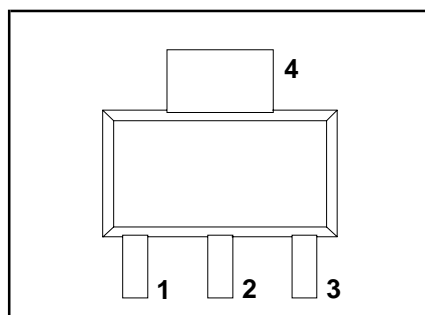
QUICK REFERENCE DATA

| SYMBOL | PARAMETER | MAX. | UNIT |
|--------------|---|------|------|
| V_{DS} | Drain-source voltage | 55 | V |
| I_D | Drain current (DC) $T_{sp} = 25\text{ °C}$ | 10.7 | A |
| | Drain current (DC) $T_{amb} = 25\text{ °C}$ | 4.9 | A |
| P_{tot} | Total power dissipation | 8.3 | W |
| T_j | Junction temperature | 150 | °C |
| $R_{DS(ON)}$ | Drain-source on-state resistance $V_{GS} = 10\text{ V}$ | 40 | mΩ |

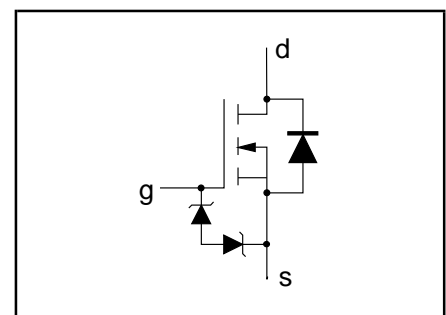
PINNING - SOT223

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | gate |
| 2 | drain |
| 3 | source |
| 4 | drain (tab) |

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|----------------|----------------------------------|------------------------------|------|------|------|
| V_{DS} | Drain-source voltage | - | - | 55 | V |
| V_{DGR} | Drain-gate voltage | $R_{GS} = 20\text{ k}\Omega$ | - | 55 | V |
| $\pm V_{GS}$ | Gate-source voltage | - | - | 20 | V |
| I_D | Drain current (DC) | $T_{sp} = 25\text{ °C}$ | - | 10.7 | A |
| | | $T_{amb} = 25\text{ °C}$ | - | 4.9 | A |
| I_D | Drain current (DC) | $T_{sp} = 100\text{ °C}$ | - | 7.5 | A |
| | | $T_{amb} = 100\text{ °C}$ | - | 3.4 | A |
| I_{DM} | Drain current (pulse peak value) | $T_{sp} = 25\text{ °C}$ | - | 42 | A |
| | | $T_{amb} = 25\text{ °C}$ | - | 19 | A |
| P_{tot} | Total power dissipation | $T_{sp} = 25\text{ °C}$ | - | 8.3 | W |
| | | $T_{amb} = 25\text{ °C}$ | - | 1.8 | W |
| T_{stg}, T_j | Storage & operating temperature | - | - 55 | 150 | °C |

ESD LIMITING VALUE

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|--------|---|-----------------------------------|------|------|------|
| V_C | Electrostatic discharge capacitor voltage | Human body model (100 pF, 1.5 kΩ) | - | 2 | kV |

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PHT11N06T

THERMAL RESISTANCES

| SYMBOL | PARAMETER | CONDITIONS | TYP. | MAX. | UNIT |
|-----------------|-------------------------------|--------------------------|------|------|------|
| $R_{th\ j-sp}$ | From junction to solder point | Mounted on any PCB | 12 | 15 | K/W |
| $R_{th\ j-amb}$ | From junction to ambient | Mounted on PCB of Fig.19 | - | 70 | K/W |

STATIC CHARACTERISTICS

$T_j = 25^\circ\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-------------------|----------------------------------|--|-----------------|---------------|-----------------|--------------------------|
| $V_{(BR)DSS}$ | Drain-source breakdown voltage | $V_{GS} = 0\text{ V}; I_D = 0.25\text{ mA}$ $T_j = -55^\circ\text{C}$ | 55 50 | - - | - - | V V |
| $V_{GS(TO)}$ | Gate threshold voltage | $V_{DS} = V_{GS}; I_D = 1\text{ mA}$ $T_j = 150^\circ\text{C}$ $T_j = -55^\circ\text{C}$ | 2.0 1.2 - | 3.0 - - | 4.0 - 4.4 | V V V |
| I_{DSS} | Zero gate voltage drain current | $V_{DS} = 55\text{ V}; V_{GS} = 0\text{ V};$ $T_j = 150^\circ\text{C}$ | - | 0.05 | 10 | μA |
| I_{GSS} | Gate source leakage current | $V_{GS} = \pm 10\text{ V}$ $T_j = 150^\circ\text{C}$ | - | 0.04 | 1 | μA |
| $\pm V_{(BR)GSS}$ | Gate source breakdown voltage | $I_G = \pm 1\text{ mA}$ $T_j = 150^\circ\text{C}$ | 16 | - | - | V |
| $R_{DS(ON)}$ | Drain-source on-state resistance | $V_{GS} = 10\text{ V}; I_D = 5\text{ A}$ $T_j = 150^\circ\text{C}$ | - | 30 | 40 | m Ω m Ω |

DYNAMIC CHARACTERISTICS

$T_{mb} = 25^\circ\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|--------------|----------------------------|---|------|------|------|------|
| g_{fs} | Forward transconductance | $V_{DS} = 25\text{ V}; I_D = 5\text{ A}; T_j = 25^\circ\text{C}$ | 3 | 12 | - | S |
| $Q_{g(tot)}$ | Total gate charge | $I_D = 9\text{ A}; V_{DD} = 44\text{ V}; V_{GS} = 10\text{ V}$ | - | 18 | - | nC |
| Q_{gs} | Gate-source charge | | - | 4.5 | - | nC |
| Q_{gd} | Gate-drain (Miller) charge | | - | 10 | - | nC |
| C_{iss} | Input capacitance | $V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V}; f = 1\text{ MHz}$ | - | 700 | 880 | pF |
| C_{oss} | Output capacitance | | - | 200 | 240 | pF |
| C_{rss} | Feedback capacitance | | - | 100 | 140 | pF |
| $t_{d\ on}$ | Turn-on delay time | $V_{DD} = 30\text{ V}; I_D = 9\text{ A};$ $V_{GS} = 10\text{ V}; R_g = 10\ \Omega$ $T_j = 25^\circ\text{C}$ | - | 15 | 23 | ns |
| t_r | Turn-on rise time | | - | 50 | 75 | ns |
| $t_{d\ off}$ | Turn-off delay time | | - | 33 | 50 | ns |
| t_f | Turn-off fall time | | - | 20 | 30 | ns |

REVERSE DIODE LIMITING VALUES AND CHARACTERISTICS

$T_j = -55$ to 175°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-----------|----------------------------------|--|------|------|------|---------------|
| I_{DR} | Continuous reverse drain current | $T_{sp} = 25^\circ\text{C}$ | - | - | 10.7 | A |
| I_{DRM} | Pulsed reverse drain current | $T_{sp} = 25^\circ\text{C}$ | - | - | 40 | A |
| V_{SD} | Diode forward voltage | $I_F = 5\text{ A}; V_{GS} = 0\text{ V}$ | - | 0.85 | 1.1 | V |
| t_{rr} | Reverse recovery time | $I_F = 5\text{ A}; -di_F/dt = 100\text{ A}/\mu\text{s};$ $V_{GS} = -10\text{ V}; V_R = 30\text{ V}$ | - | 45 | - | ns |
| Q_{rr} | Reverse recovery charge | | - | 0.3 | - | μC |

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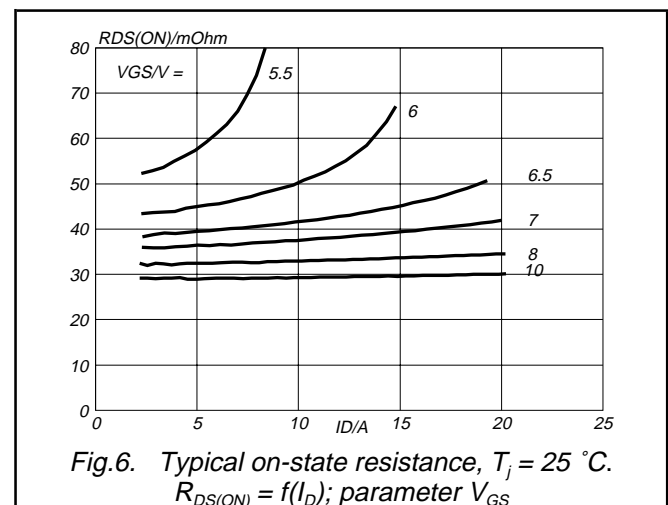
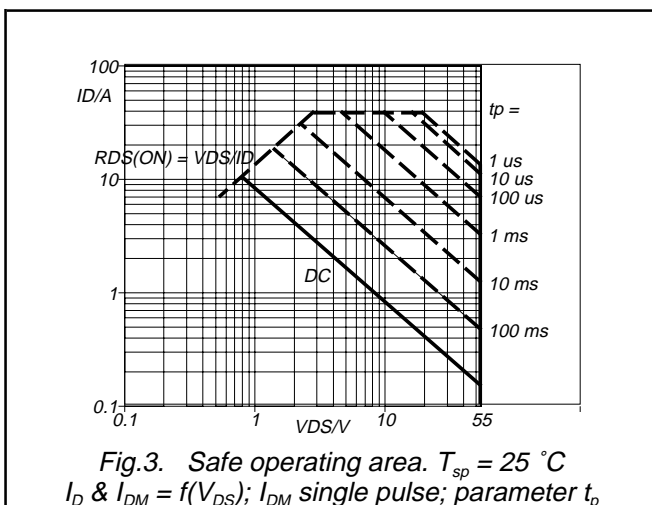
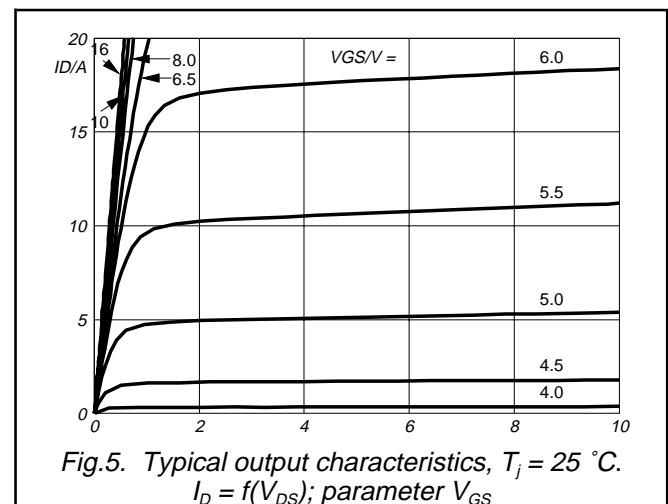
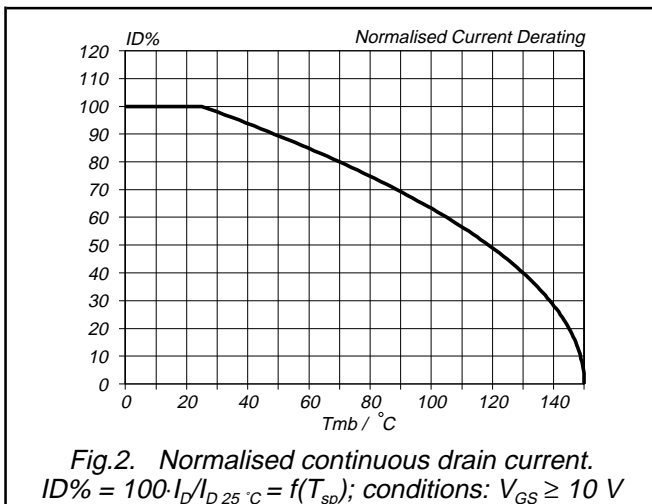
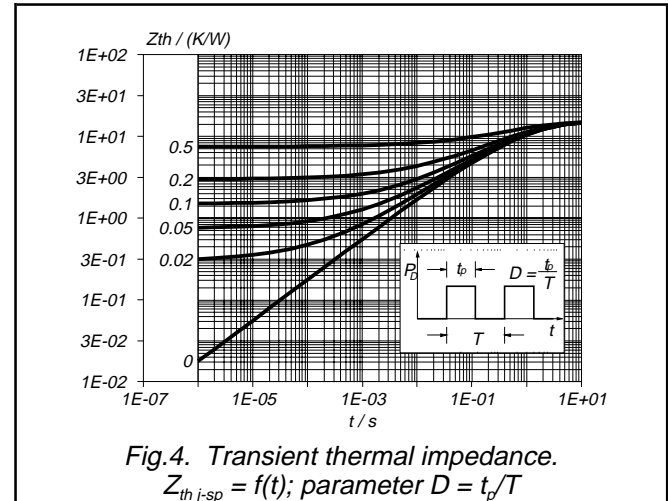
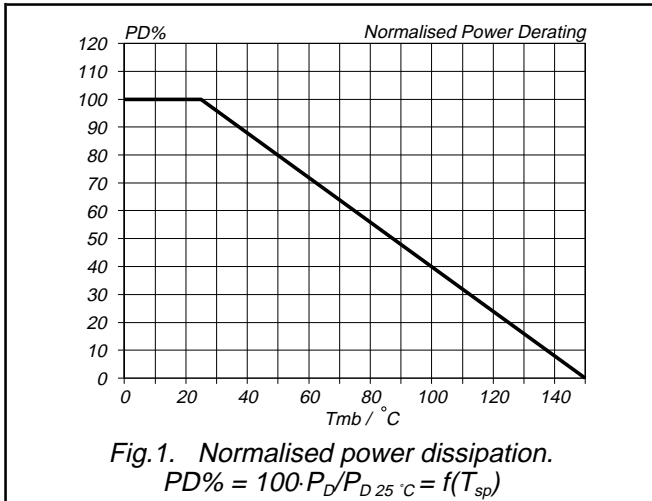
PHT11N06T

AVALANCHE LIMITING VALUE

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-----------|---|---|------|------|------|------|
| W_{DSS} | Drain-source non-repetitive unclamped inductive turn-off energy | $I_D = 3.6 \text{ A}$; $V_{DD} \leq 25 \text{ V}$; $V_{GS} = 10 \text{ V}$; $R_{GS} = 50 \text{ } \Omega$; $T_{sp} = 25 \text{ } ^\circ\text{C}$ | - | - | 60 | mJ |

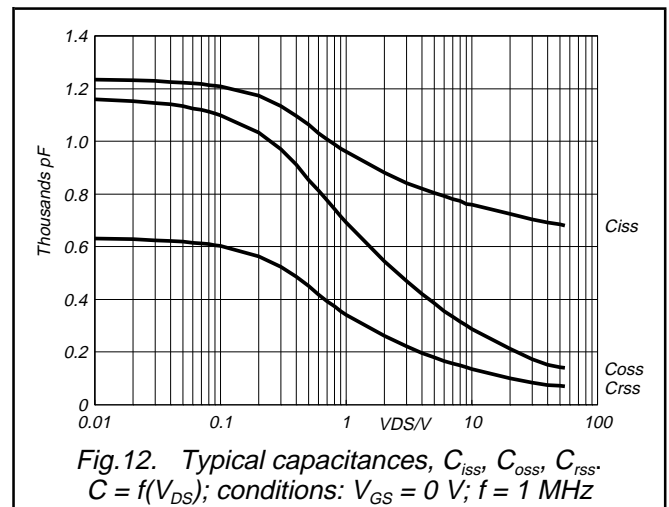
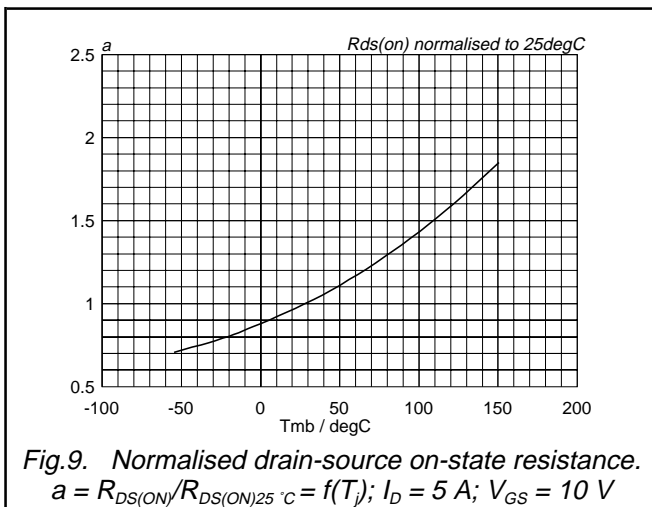
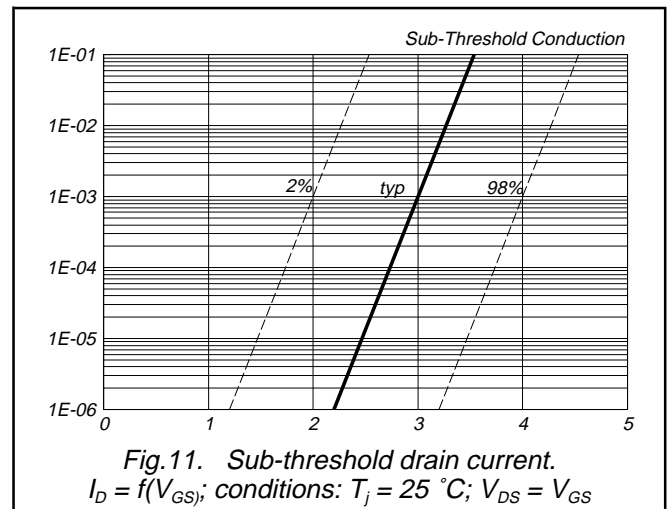
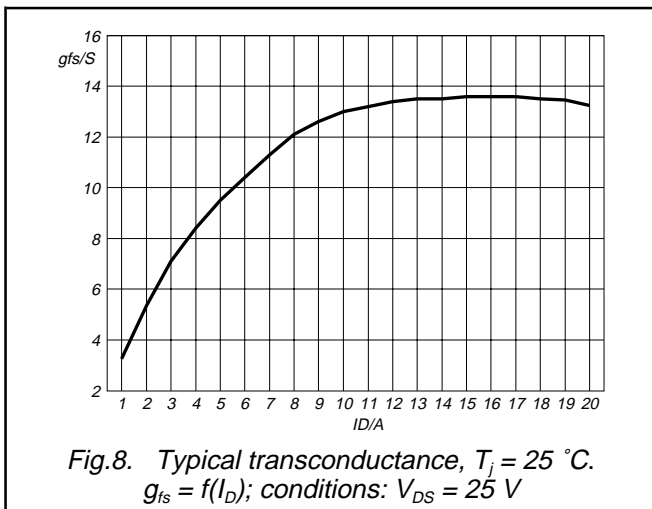
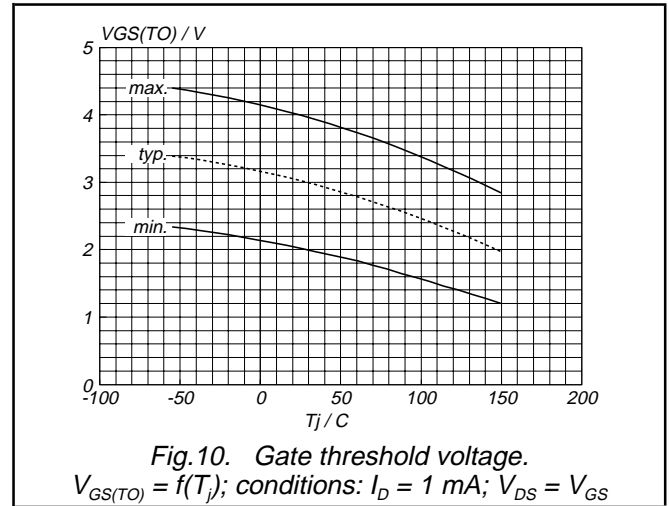
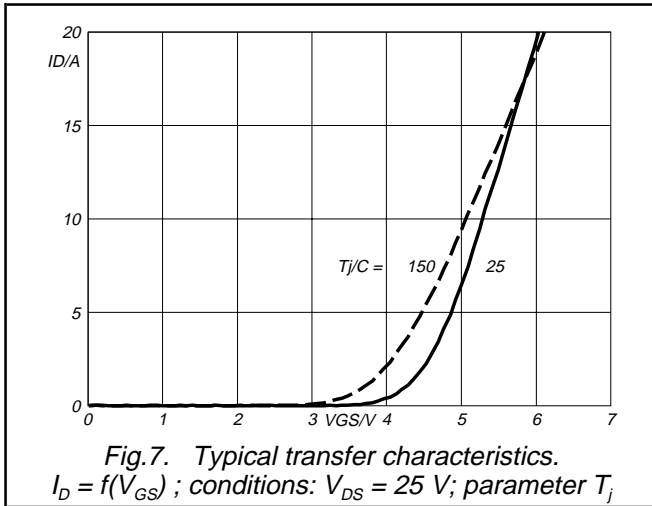
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PHT11N06T



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Standard level FET

PHT11N06T

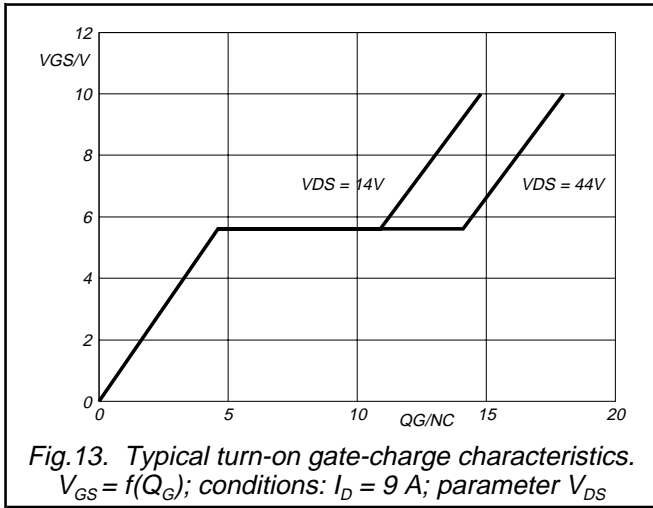


Fig. 13. Typical turn-on gate-charge characteristics.
 $V_{GS} = f(Q_G)$; conditions: $I_D = 9 A$; parameter V_{DS}

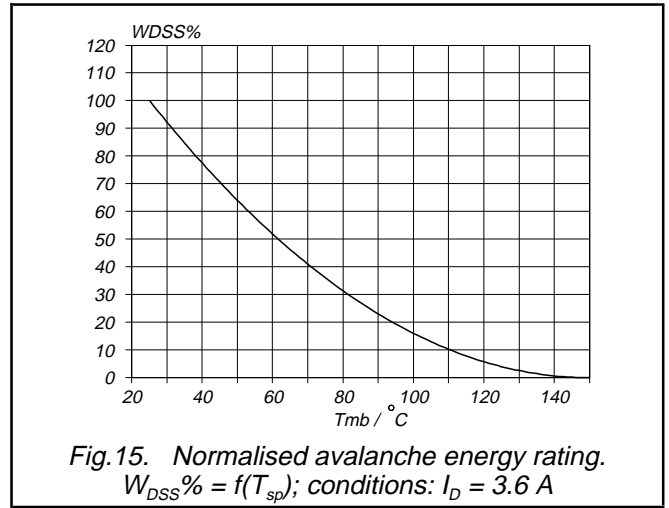


Fig. 15. Normalised avalanche energy rating.
 $W_{DSS}\% = f(T_{sp})$; conditions: $I_D = 3.6 A$

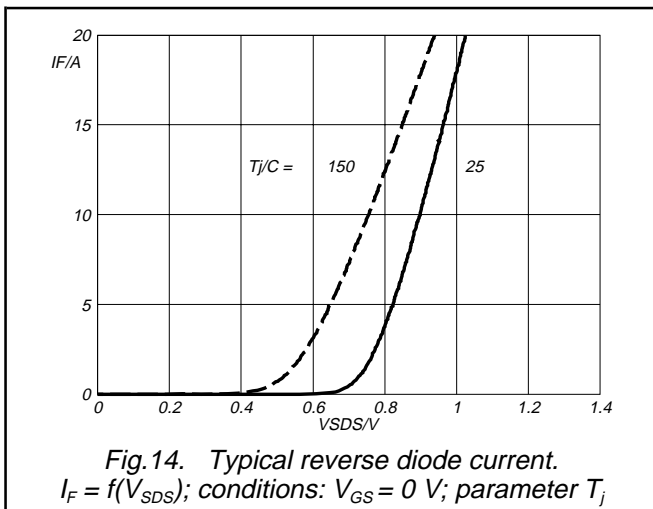


Fig. 14. Typical reverse diode current.
 $I_F = f(V_{SDS})$; conditions: $V_{GS} = 0 V$; parameter T_j

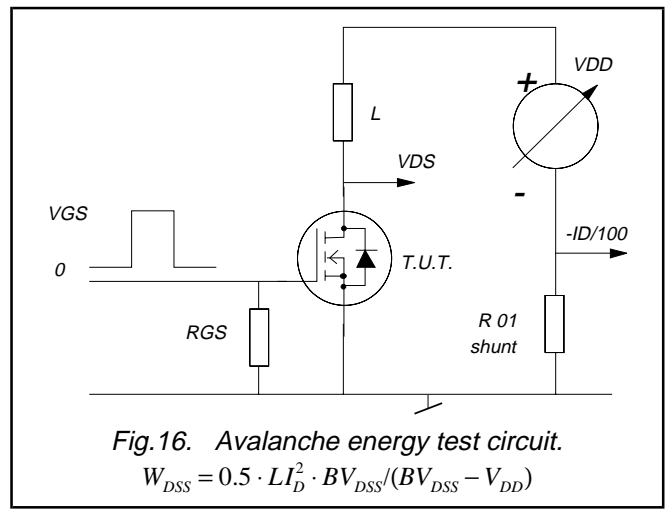


Fig. 16. Avalanche energy test circuit.
 $W_{DSS} = 0.5 \cdot L I_D^2 \cdot BV_{DSS} / (BV_{DSS} - V_{DD})$

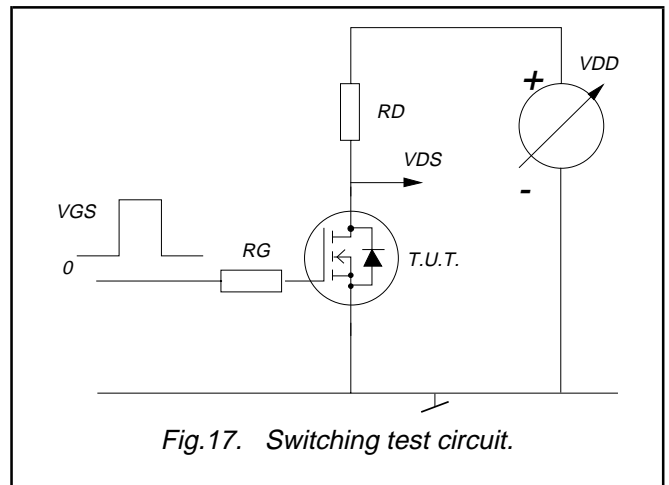


Fig. 17. Switching test circuit.

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MOUNTING INSTRUCTIONS

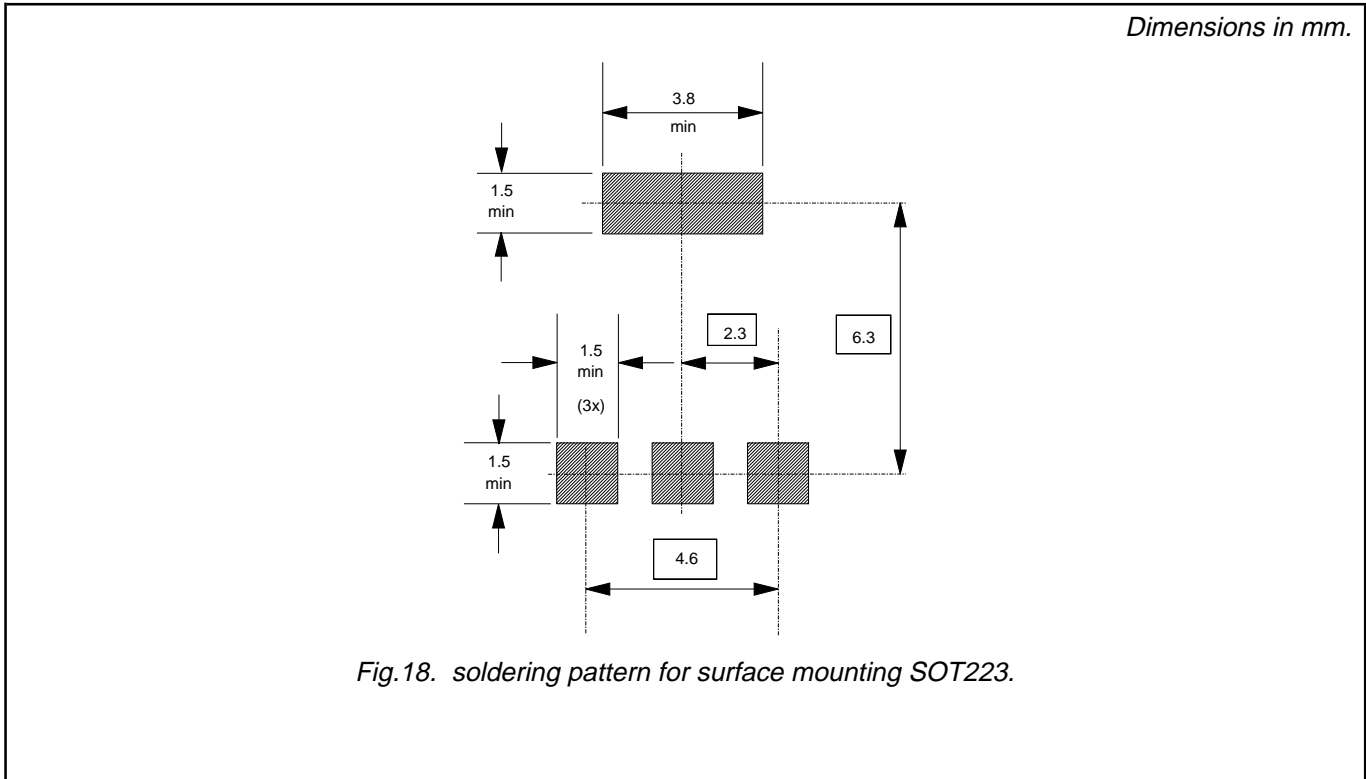
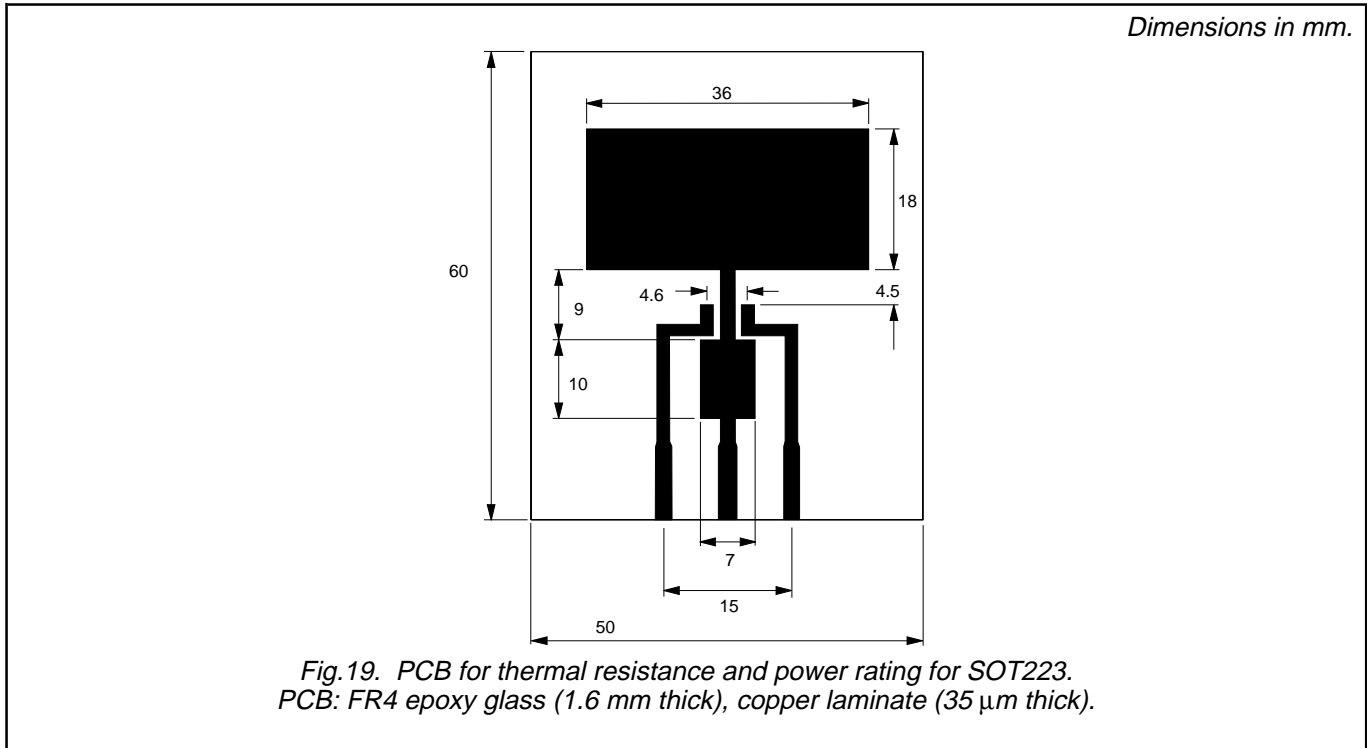


Fig.18. soldering pattern for surface mounting SOT223.

PRINTED CIRCUIT BOARD

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Standard level FET

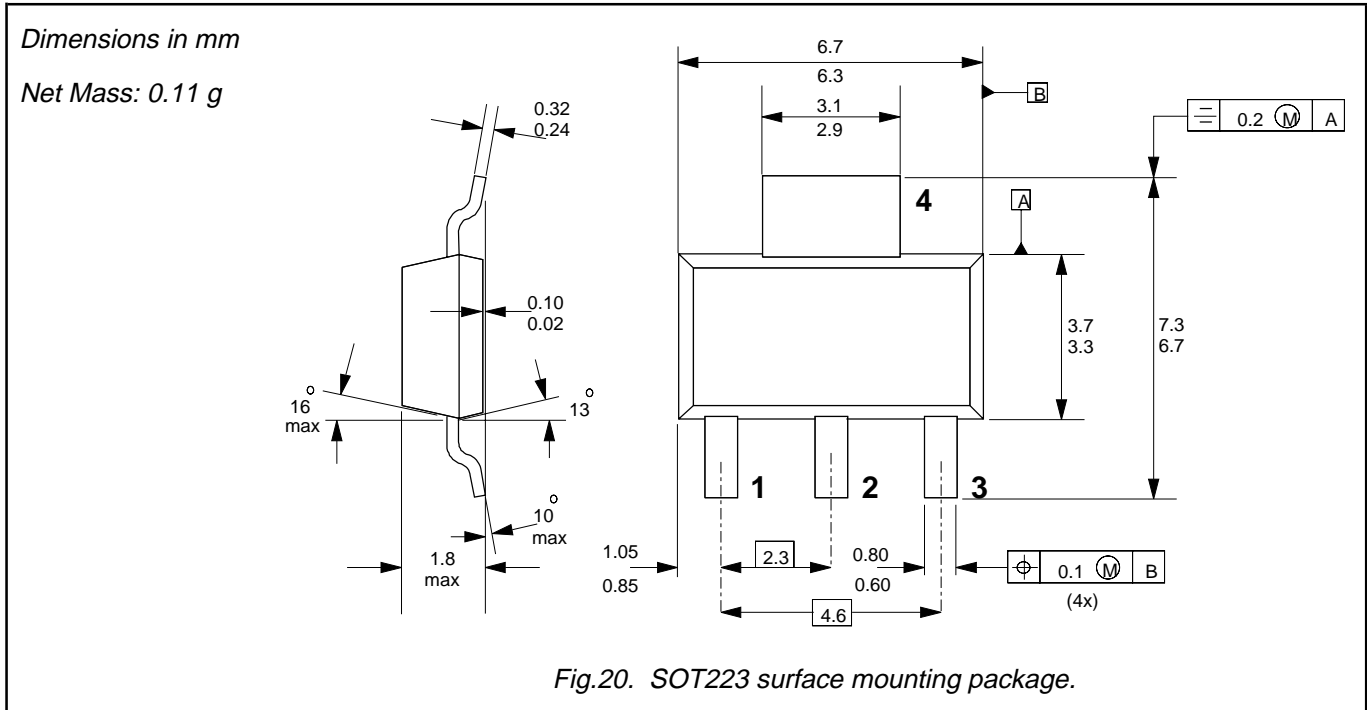
PHT11N06T



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PHT11N06T

MECHANICAL DATA



Notes

1. Observe the general handling precautions for electrostatic-discharge sensitive devices (ESDs) to prevent damage to MOS gate oxide.
2. Refer to surface mounting instructions for SOT223 envelope.
3. Epoxy meets UL94 V0 at 1/8".

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DEFINITIONS

| | |
|--|---|
| Data sheet status | |
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| Limiting values | |
| Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability. | |
| Application information | |
| Where application information is given, it is advisory and does not form part of the specification. | |
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